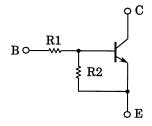
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

RN1130FV

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications

- Built-in bias resistors
- Simplified circuit design
- Reduced quantity of parts and manufacturing process
- Complementary to RN2130FV

Equivalent Circuit



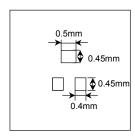
Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit	
Collector-base voltage	V_{CBO}	50	V	
Collector-emitter voltage	V _{CEO}	50	V	
Emitter-base voltage	V _{EBO}	10	V	
Collector current	IC	100	mA	
Collector power dissipation	P _C (Note)	150	mW	
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	−55~150	°C	

Note: Mounted on FR4 board (25.4 mm \times 25.4 mm \times 1.6 mmt)

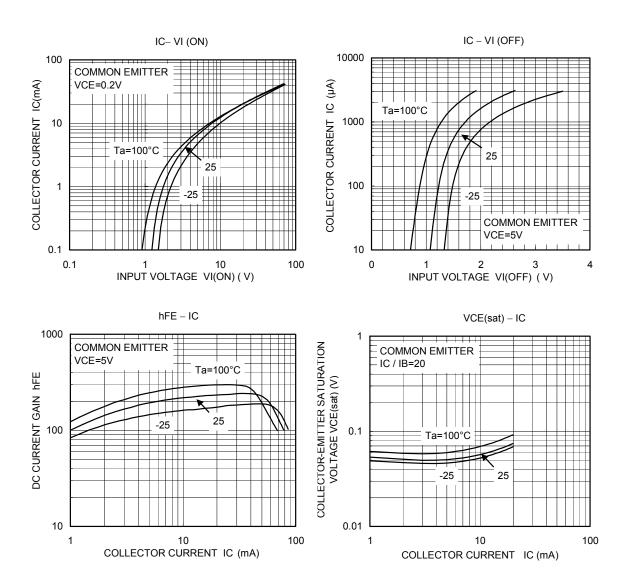
1.2±0.05 0.8

Weight: 0.0015 g (typ.)



Electrical Characteristics (Ta = 25°C)

Characteristic	Cumbal	Toot Condition	Min	Tun	Mov	Linit
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 50V, I_{E} = 0$	_	_	100	nA
	I _{CEO}	V _{CB} = 50V, I _B = 0	_	_	500	nA
Emitter cut-off current	I _{EBO}	V _{EB} = 10V, I _C = 0	38	_	72	uA
DC current gain	h _{FE}	V _{CE} = 5V, I _C = 10mA	100	_	-	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 5mA, I _B = 0.25mA	_	0.1	0.3	V
Input voltage(ON)	V _{I(ON)}	V _{CE} = 0.2V, I _C = 5mA	1.7	_	8.2	V
Input voltage(OFF)	V _{I(OFF)}	$V_{CE} = 5V, I_{C} = 0.1mA$	1.0	_	1.6	V
Transition frequency	f _T	V _{CE} = 10V, I _C = 5mA	_	250	_	MH_{Z}
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MH _Z	_	3	_	pF
Input resistance	R1	_	70	100	130	kΩ
Resistance ratio	R1/R2	_	0.8	1.0	1.2	



Type Name	Marking	
RN1130FV	Type Name	

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